Abstract of the Disclosure

The present invention provides a method of fabricating a capacitor for a semiconductor device. The method includes: forming sequentially a lower electrode and a dielectric layer having a high dielectric constant over a semiconductor substrate which have gone through predetermined processes; forming sequentially a first metal layer and a poly-silicon layer over the dielectric layer; forming an upper electrode pattern by pattering the poly-silicon layer and the first metal layer; forming a second metal layer covering the upper electrode pattern on an entire surface of the semiconductor substrate; and forming an upper electrode constituted with the second metal layer, the poly-silicon layer and the first metal layer by patterning the second metal layer so that the second metal layer is connected with the first metal layer.